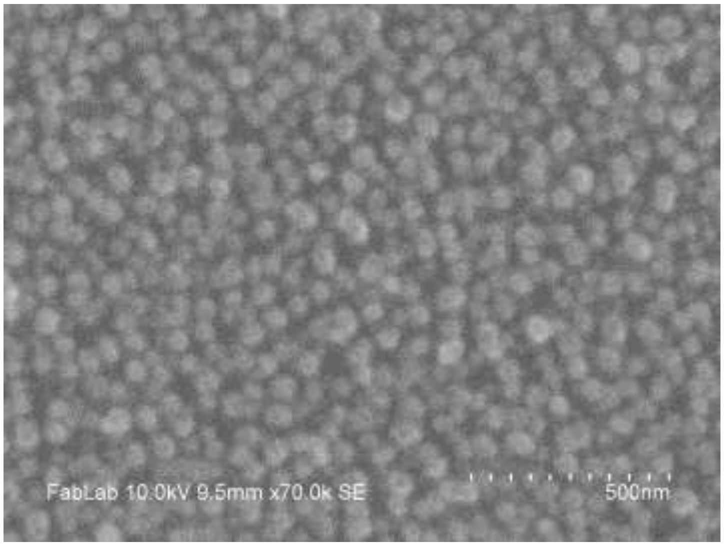

Figure 1. Scanning electron image of the reduced NiO thin-film. Reduction is performed using molecular hydrogen balanced with argon at 400^{oC}.

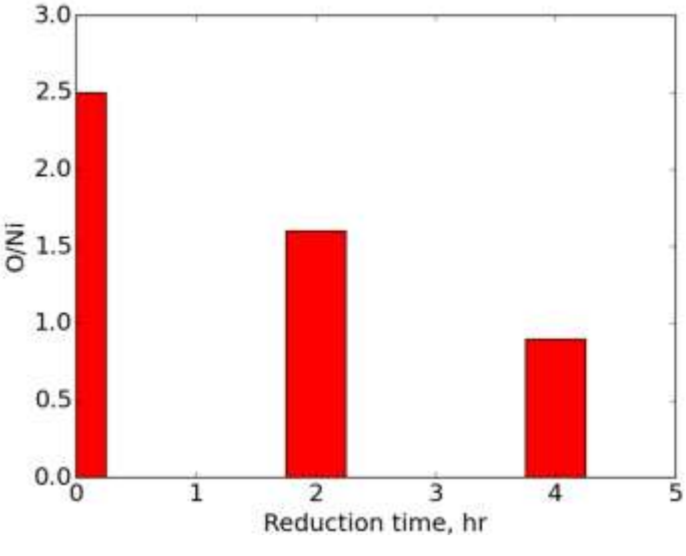

Figure 2. Effect of the reduction process time on the O/Ni ratio of the ALD deposited NiO film measured by energy dispersive spectroscopy. The oxygen content is overestimated due to native oxide layer on the substrate.